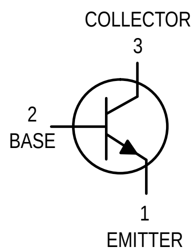
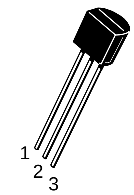
General Purpose Transistors

NPN Silicon

2N4264
2N4265





CASE 29–04, STYLE 1
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	2N4264	2N4265	Unit
Collector–Emitter Voltage	V_{CEO}	15	12	Vdc
Collector–Base Voltage	V_{CBO}	30		Vdc
Emitter–Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0) 2N4264 2N4265	$V_{(BR)CEO}$	 15 12	 — —	Vdc
Collector–Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	30	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current (V_{CE} = 12 Vdc, $V_{EB(off)}$ = 0.25 Vdc) (V_{CE} = 12 Vdc, $V_{EB(off)}$ = 0.25 Vdc, T_A = 100°C)	I_{BEV}	 — —	 0.1 10	μAdc
Collector Cutoff Current (V_{CE} = 12 Vdc, $V_{EB(off)}$ = 0.25 Vdc)	I_{CEX}	—	100	nAdc

REV 1

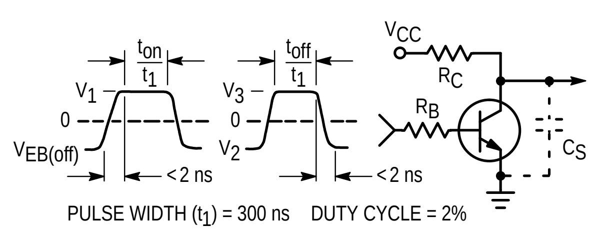
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)	2N4264		25	—	
	2N4265		50	—	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	2N4264		40	160	
	2N4265		100	400	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc, T_A = –55°C)	2N4264		20	—	
	2N4265		45	—	
(I_C = 30 mAdc, V_{CE} = 1.0 Vdc)	2N4264		40	—	
	2N4265		90	—	
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)(1)	2N4264		30	—	
	2N4265		55	—	
(I_C = 200 mAdc, V_{CE} = 1.0 Vdc)(1)	2N4264		20	—	
	2N4265		55	—	
Collector–Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			—	0.22	
(I_C = 100 mAdc, I_B = 10 mAdc)(1)			—	0.35	
Base–Emitter Saturation Voltage		$V_{BE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			0.65	0.8	
(I_C = 100 mAdc, I_B = 10 mAdc)(1)			0.75	0.95	
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	300	—	MHz
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	8.0	pF
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz, I_E = 0)		C_{obo}	—	4.0	pF
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 10 Vdc, $V_{EB(off)}$ = 2.0 Vdc, I_C = 100 mAdc, I_{B1} = 10 mAdc) (Fig. 1, Test Condition C)	t_d	—	8.0	ns
Rise Time		t_r	—	15	ns
Storage Time	V_{CC} = 10 Vdc, (I_C = 10 mAdc, for t_s) (I_C = 100 mA for t_f) (I_{B1} = –10 mA) (I_{B2} = 10 mA) (Fig. 1, Test Condition C)	t_s	—	20	ns
Fall Time		t_f	—	15	ns
Turn–On Time	(V_{CC} = 3.0 Vdc, $V_{EB(off)}$ = 1.5 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc) (Fig. 1, Test Condition A)	t_{on}	—	25	ns
Turn–Off Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc, I_{B2} = 1.5 mAdc) (Fig. 1, Test Condition A)	t_{off}	—	35	ns
Storage Time	(V_{CC} = 10 Vdc, I_C = 10 mA, I_{B1} = I_{B2} = 10 mAdc) (Fig. 1, Test Condition B)	t_s	—	20	ns
Total Control Charge	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_B = mAdc) (Fig. 3, Test Condition A)	Q_T	—	80	pC

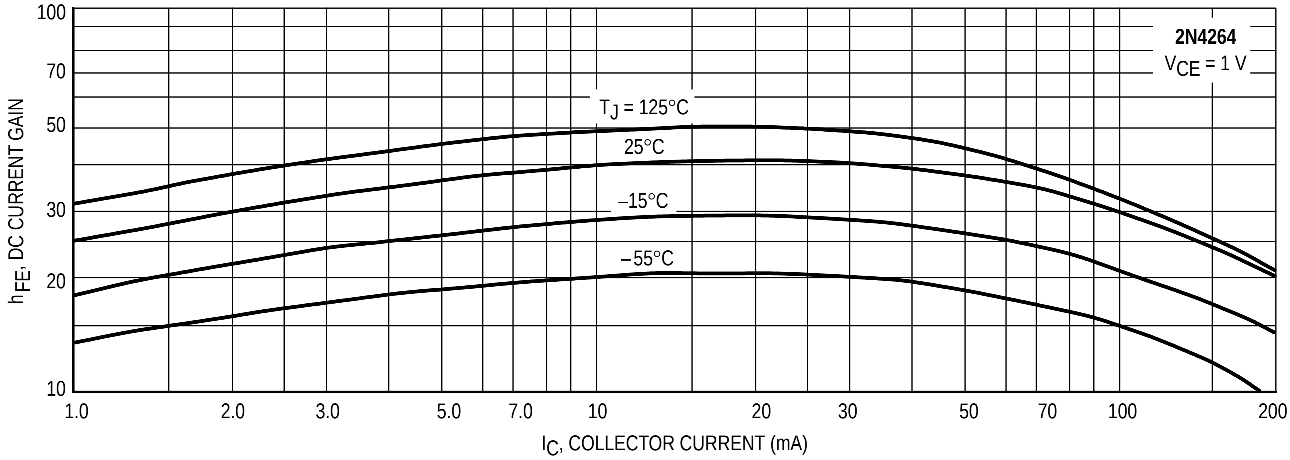
1. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

Figure 1. Switching Time Equivalent Test Circuit

Test Condition	I_C	V_{CC}	R_S	R_C	$C_{S(max)}$	$V_{BE(off)}$	V_1	V_2	V_3
	mA	V	Ω	Ω	pF	V	V	V	V
A	10	3	3300	270	4	–1.5	10.55	–4.15	10.70
B	10	10	560	960	4	—	—	–4.65	6.55
C	100	10	560	96	12	–2.0	6.35	–4.65	6.55



CURRENT GAIN CHARACTERISTICS



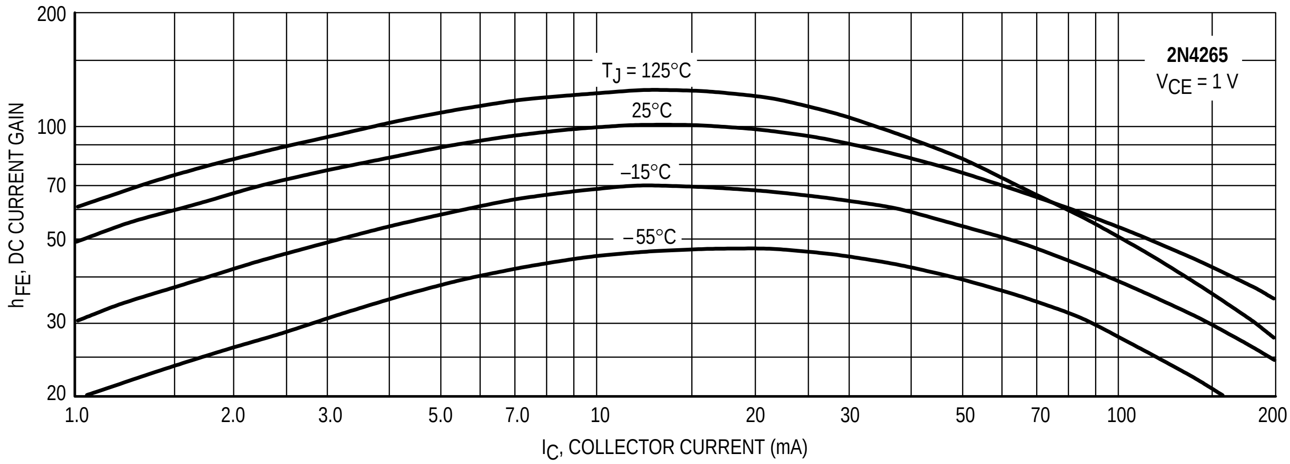


Figure 2. Minimum Current Gain

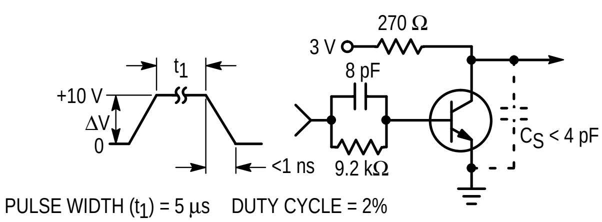


Figure 3. Q_T Test Circuit

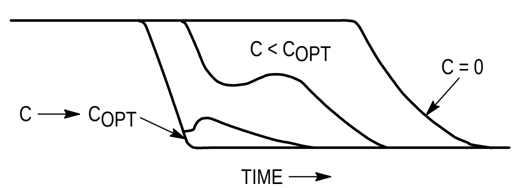


Figure 4. Turn–Off Waveform

NOTE 1

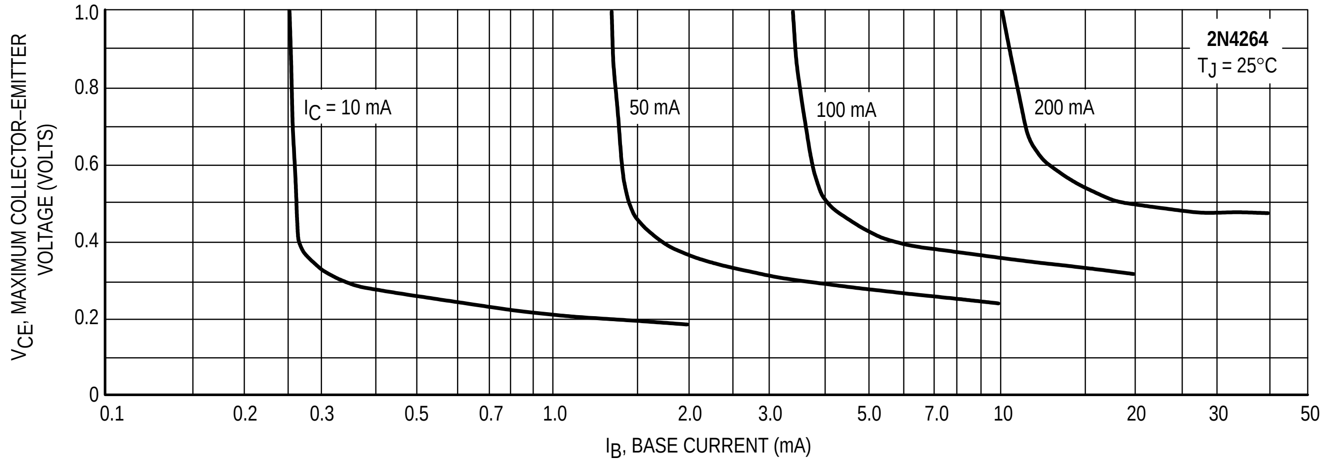
When a transistor is held in a conductive state by a base current, I_B, a charge, Q_S, is developed or “stored” in the transistor. Q_S may be written: $Q_S = Q_1 + Q_V + Q_X$.

Q_1 is the charge required to develop the required collector current. This charge is primarily a function of alpha cutoff frequency. Q_V is the charge required to charge the collector–base feedback capacity. Q_X is excess charge resulting from overdrive, i.e., operation in saturation.

The charge required to turn a transistor “on” to the edge of saturation is the sum of Q_1 and Q_V which is defined as the active region charge, Q_A. $Q_A = I_{B1}t_r$ when the transistor is driven by a constant current step (I_{B1}) and $I_{B1} << \frac{I_C}{h_{FE}}$.

If I_B were suddenly removed, the transistor would continue to conduct until Q_S is removed from the active regions through an external path or through internal recombination. Since the internal recombination time is long compared to the ultimate capability of a transistor, a charge, Q_T, of opposite polarity, equal in magnitude, can be stored on an external capacitor, C, to neutralize the internal charge and considerably reduce the turn–off time of the transistor. Figure 3 shows the test circuit and Figure 4 the turn–off waveform. Given Q_T from Figure 13, the external C for worst–case turn–off in any circuit is: $C = Q_T/\Delta V$, where ΔV is defined in Figure 3.

"ON" CONDITION CHARACTERISTICS



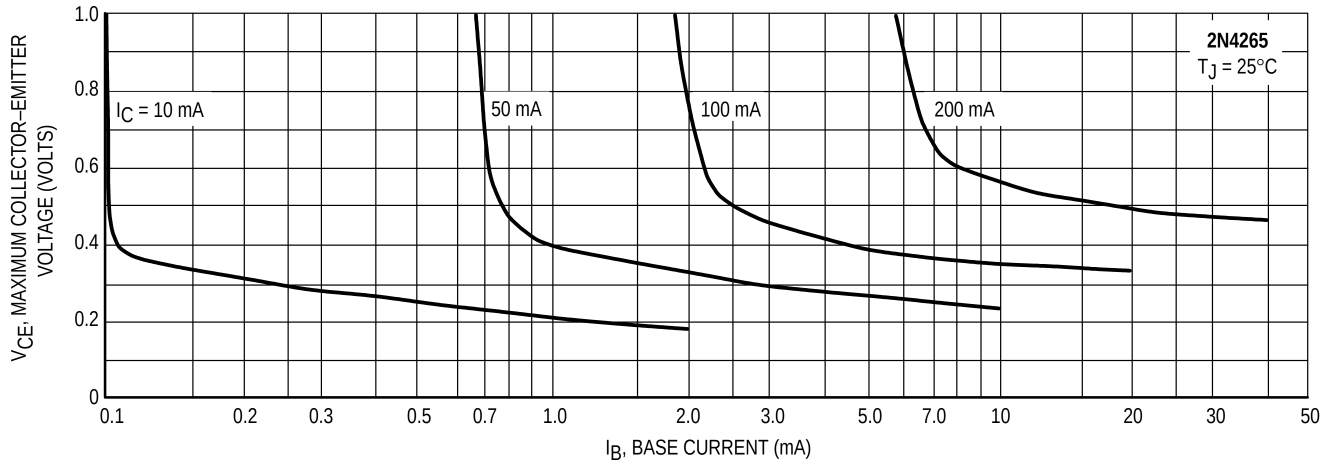


Figure 5. Collector Saturation Region

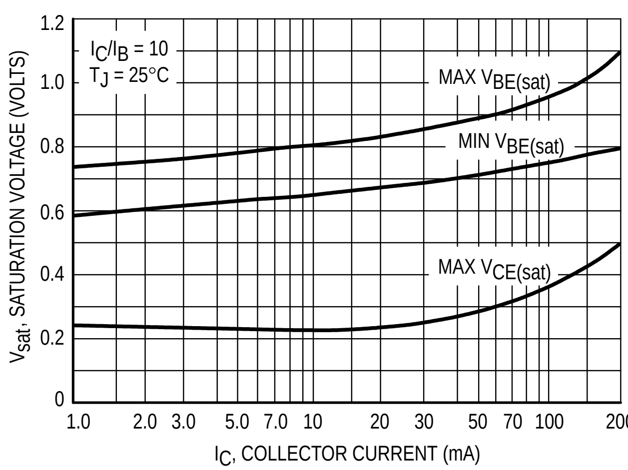


Figure 6. Saturation Voltage Limits

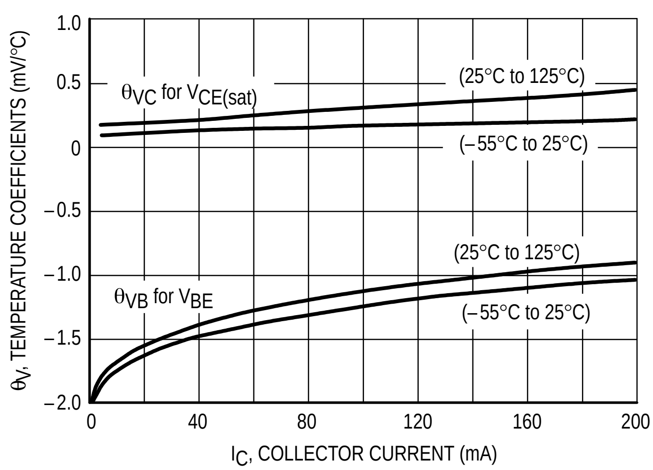


Figure 7. Temperature Coefficients

DYNAMIC CHARACTERISTICS

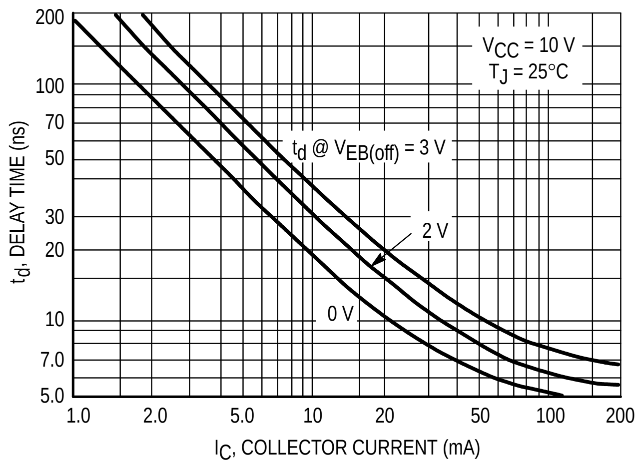


Figure 8. Delay Time

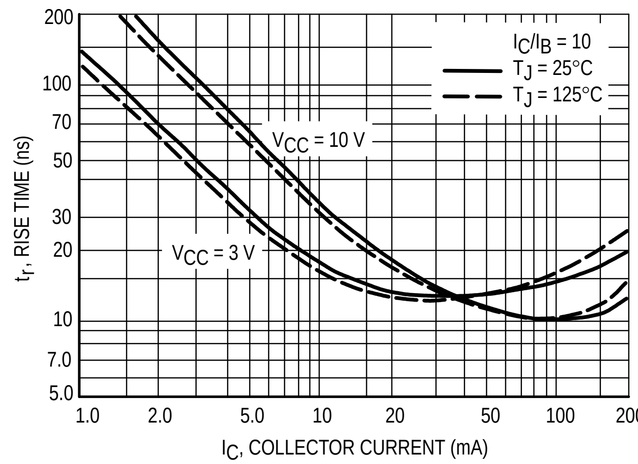


Figure 9. Rise Time

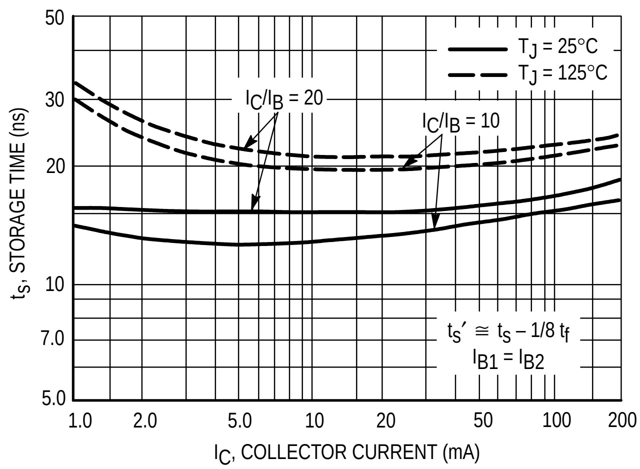


Figure 10. Storage Time

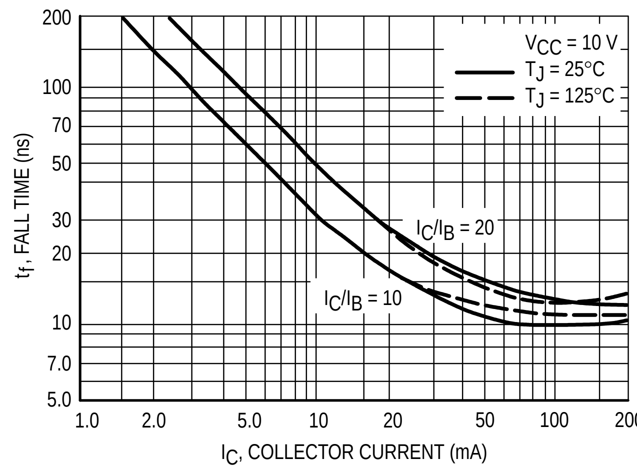


Figure 11. Fall Time

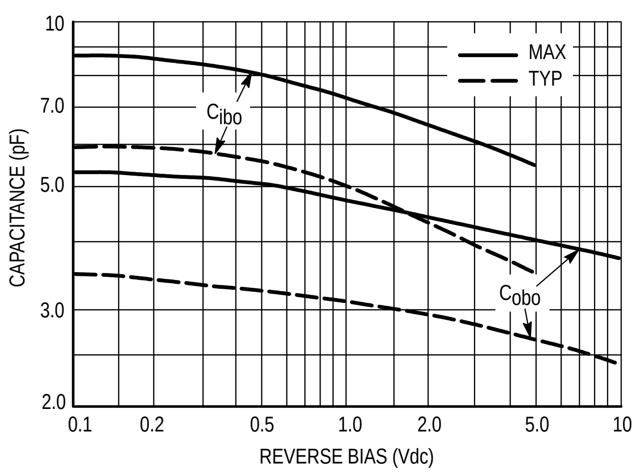


Figure 12. Junction Capacitance

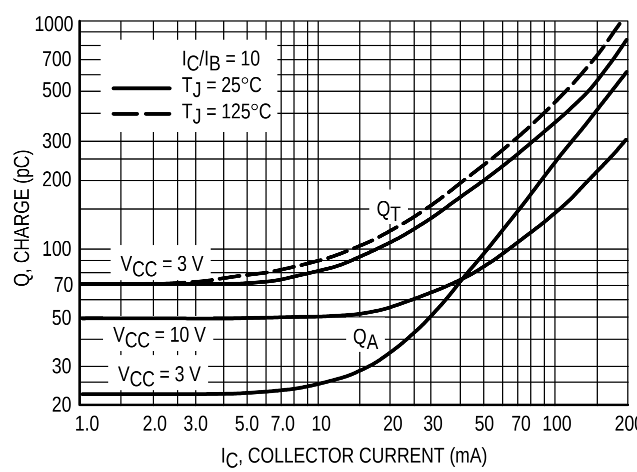
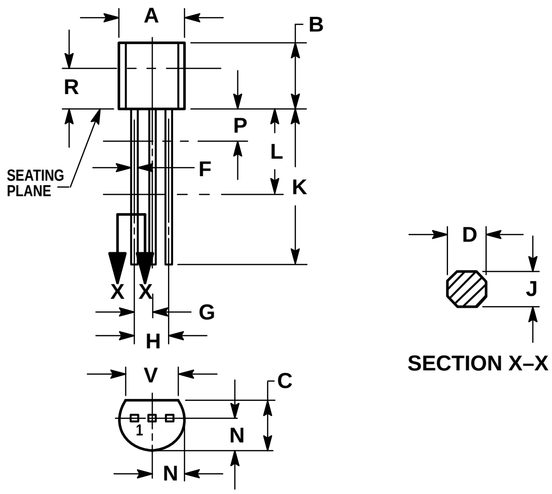


Figure 13. Maximum Charge Data

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	——	12.70	——
L	0.250	——	6.35	——
N	0.080	0.105	2.04	2.66
P	——	0.100	——	2.54
R	0.115	——	2.93	——
V	0.135	——	3.43	——

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

CASE 029–04
(TO–226AA)
ISSUE AD

How to reach us:
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P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447

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JAPAN: Nippon Motorola Ltd.; Tatsumi–SPD–JLDC, Toshikatsu Otsuki,
6F Seibu–Butsuryu–Center, 3–14–2 Tatsumi Koto–Ku, Tokyo 135, Japan. 03–3521–8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298